Central™
Semiconductor Corp.
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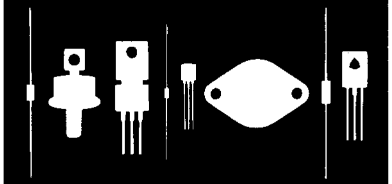

1N625 1N626
1N627 1N628
1N629

SILICON SWITCHING DIODES

JEDEC DO-7 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N625 series types are silicon diodes designed for medium speed switching applications.

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

	SYMBOL	1N625	1N626	1N627	1N628	1N629	UNIT
Peak Working Reverse Voltage	V_{RWM}	20	35	75	125	175	V
Average Forward Current	I_O	20	20	20	20	20	V
Average Forward Current (T_A=100°C)	I_O	5.0	5.0	5.0	5.0	5.0	mA
Peak Foward Surge Current	I_{FSM}	500	500	500	500	500	mA
Power Dissipation	P_D	400	400	400	400	400	mW
Operating and Storage Junction Temperature	T_J, T_{STG}			-65 TO +200			°C

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

		1N625		1N626		1N627		1N628		1N629		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
I_R	V_R=Rated V_{RWM}		1.0		1.0		1.0		1.0		1.0	µA
I_R	V_R=Rated V_{RWM}, T_A=100°C		30		30		30		30		30	µA
BV_R	I_R=100µA	30		50		100		150		200		V
V_F	I_F=4.0mA		1.5		1.5		1.5		1.5		1.5	V
t_{rr}	V_R=35V, I_F=30mA, C_L=20pF, R_L=25kΩ, Recovery to 400kΩ		1.0		1.0		1.0		1.0		1.0	µs

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